TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

## 2SA1431

# Strobe Flash Applications Medium Power Amplifier Applications

 $\bullet \quad \mbox{High DC}$  current gain and excellent  $\mbox{hFE}$  linearity

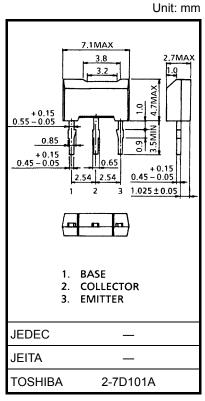
 $h_{FE(1)} = 100 \text{ to } 320 \text{ (V}_{CE} = -2 \text{ V, I}_{C} = -0.5 \text{ A}$ 

 $h_{FE(2)} = 70 \text{ (min) } (V_{CE} = -2 \text{ V}, I_{C} = -4 \text{ A})$ 

• Low saturation voltage: VCE (sat) = -1.0 V (max)(IC = -4 A, IB = -0.1 A)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		$V_{CBO}$	-35	V	
Collector-emitter voltage		V <sub>CEO</sub>	-20	V	
Emitter-base voltage		V <sub>EBO</sub>	-8	V	
Collector current	DC	IC	-5	Α	
	Pulsed (Note 1)	I <sub>CP</sub>	-8		
Base current		ΙΒ	-0.5	Α	
Collector power dissipation		PC	1000	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 0.2 g (typ.)

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

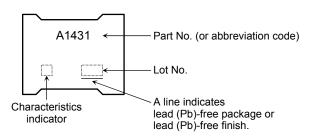
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

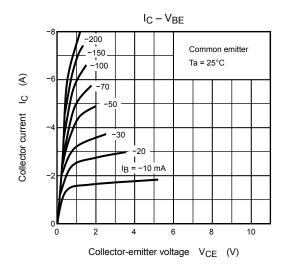
## **Electrical Characteristics (Ta = 25°C)**

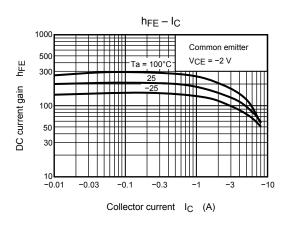
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -35 \text{ V}, I_{E} = 0$	_	_	-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -8 V, I <sub>C</sub> = 0	_	_	-100	nA
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-20	_	_	٧
Emitter-base breakdown voltage	V (BR) EBO	$I_E = -1 \text{ mA}, I_C = 0$	-8	_	_	٧
DC current gain	h <sub>FE (1)</sub> (Note 3)	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	100	_	320	
	h <sub>FE</sub> (2)	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -4 A	70	_	_	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -4 A, I <sub>B</sub> = -0.1 A	_	_	-1.0	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -4 A	_	_	-1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	_	170	_	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	62	_	pF

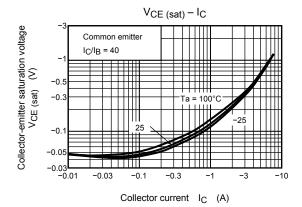
Note 3:  $h_{FE\ (1)}$  classification O: 100 to 200, Y: 160 to 320

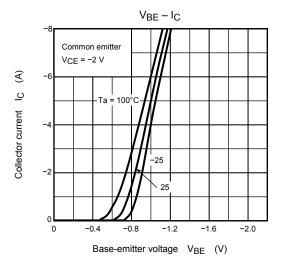
## Marking

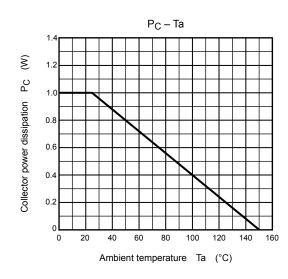


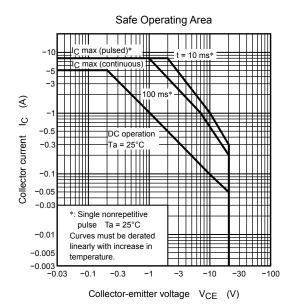












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